Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	159	(438/282).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/27 09:30
S2	599	(438/682).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 17:14
S3	263	S2 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:21
S5	746	(438/685).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 18:21
S6	149	S5 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:13
S7	8	S5 and ((ni nickel) near3 (alloy$3 near3 metal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:26
S8	850859	mos (metal adj oxide adj semiconduct$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:25
S9	25614	S8 and (silicide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:26

S10	275	S9 and ((ni nickel) near3 (alloy$3 near3 metal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:26
S11	1151	S9 and ((ni nickel) near3 (alloy$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:26
S12	4	S9 and (nickel near3 silicide near3 ((upper top) and (lower bottom)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:28
S13	1	("2004/0266182").URPN.	USPAT	OR	ON	2005/10/20 18:29
S14	0	("2004/0209432").URPN.	USPAT	OR	ON	2005/10/20 18:32
S15	0	S11 and (sbl (silicide adj block$3 adj (layer film)))	USPAT	OR	ON	2005/10/20 18:33
S16	0	S11 and (sbl (silicide adj block$3 adj layer))	USPAT	OR	ON	2005/10/20 18:34
S17	409	S11 and (cap$4)	USPAT	OR	ON	2005/10/20 18:35
S18	0	S11 and ((ion atom impurit$4) near3 implat$4)	USPAT	OR	ON	2005/10/24 16:12
S19	75	S11 and ((ion atom impurit$4) near3 implant$4)	USPAT	OR	ON	2005/10/20 18:36
S20	46	S19 and (anneal$5)	USPAT	OR	ON	2005/10/20 18:42
S21	378	(438/686).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/20 18:42
S22	142	S21 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 18:42
S23	747	(438/660).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 10:40

S24	166	S23 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 10:41
S25	76	S24 and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 12:57
S26	218	(438/663).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 12:57
S27	12	S26 and ((silicide salicide) and (ldd (light$3 adj dope$3 adj (drain source))) and (Ni nickel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 13:09
S28	1118	(438/514).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 13:09
S29	10	S28 and ((silicide salicide) and (ldd (light$3 adj dope$3 adj (drain source))) and (Ni nickel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:13
S30	22	S28 and ((silicide salicide) and (Ni nickel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:09
S31	850953	mos (metal adj oxid$3 adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:10

S32	255228	S31 and ((high$3 and low$3) and (temperat$4 anneal$4 heat$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:11
S33	11215	S32 and ((ion atom impurit$4) near3 implant$4)	USPAT	OR	ON	2005/10/24 16:12
S34	1789	S33 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/26 19:05
S35	506	S34 and ((silicide salicide) and (ldd (light$3 adj dope$3 adj (drain source))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:32
S36	6	S35 and ((reactivat$3 activat$3) and deactivat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:16
S37	275	S35 and (cap cap$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 16:33
S38	1311	(cap capping block$4 mask$4 protect$3) same (silicid$5 salicid$5) same (temperature heat$3 anneal$ thermal$2) with (degree C)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:33
S39	306	S38 and ((ni nickel) and (alloy$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 19:01
S40	203	(cap capping block$4 mask$4 protect$3) with (silicid$5 salicid$5) with (temperature heat$3 anneal$ thermal$2) with (degree C)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/24 19:02

S41	24609	(cap capping block$4 mask$4 protect$3) same (Ti titanium) same (temperature heat$3 anneal$ thermal$2) with (degree C)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:35
S42	8697	S41 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:34
S43	1246	(cap capping block$4 mask$4 protect$3) with (Ti titanium) with (temperature heat$3 anneal$ thermal$2) with (degree C)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:35
S44	79	S43 and (silicid$3 salicid$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/25 15:36
S45	2	("20020064918").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/25 19:56
S46	1	("20040123922").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/26 18:15
S47	851133	mos (metal adj oxid$3 adj semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/26 19:05
S48	255335	S47 and ((high$3 and low$3) and (temperat$4 anneal$4 heat$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/26 19:05
S49	11230	S48 and ((ion atom impurit$4) near3 implant$4)	USPAT	OR	ON	2005/10/26 19:05

S50	1794	S49 and (ni nickel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/26 19:07
S51	6	S49 and (((ni nickel) near6 alloy$3) with (((low lower bottom) and (up upper top)) near6 (layer film)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/26 19:09
S52	75	(silicid$3 salicid$3) with (ni nickel) with (((low lower bottom) and (top high up upper)) near4 (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 09:32